

30. An epitaxial growth method comprising:

placing a substrate in a system so that each side of the substrate is not completely covered by any parts or susceptor blocks;

supplying a set of reactant species on one side of the substrate without rotating the substrate;

supplying another set of reactant species on the other side of the substrate without rotating the substrate; and

preventing mixing of the two sets of reactant species.--

REMARKS

New claims 29 and 30 correspond to claims 15 and 19 as originally filed, respectively, with the additional feature that specified processes are performed "without rotating the substrate." In contrast, both Hansson (applied against claims 15 and 19) and Rohm (applied against claim 15) expressly disclose rotating the substrate during a processing. Further, Manabe et al. (applied against claim 15) is completely silent as to the mechanism by which the substrate is held during processing. Accordingly, it is respectfully submitted that none of the cited prior art discloses or suggests the **combination** of steps recited in claims 29 and 30. It is therefore submitted that claims 29 and 30 are patentable over the cited prior art.

It is believed that no extension of time is needed for entry of the above amendment as it is merely supplemental to the complete and fully responsive amendment filed on March 17, 2003.